



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

#8A *Andt.*  
M. Brunson  
8/27/02

IN RE APPLICATION OF

KAZUHIRO SHIMIZU, ET AL.

: EXAMINER: WEISS, H.

SERIAL NO: 09/925,418

:

FILED: AUGUST 10, 2001

: GROUP ART UNIT: 2814

FOR: NON-VOLATILE  
SEMICONDUCTOR MEMORY  
DEVICE HAVING MEMORY  
CELL ARRAY SUITABLE FOR  
HIGH DENSITY AND HIGH  
INTEGRATION

RECEIVED  
AUG 22 2002  
TECHNOLOGY CENTER 2800

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated May 17, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend Claims 1, 5, 6, 9, 10, and 13 as shown in clean form below.<sup>1</sup>

*Sub B1*

1. (Amended) A non-volatile semiconductor memory device comprising:  
a semiconductor body of a first conductivity type;  
first and second semiconductor regions of a second conductivity type, formed apart  
from each other on the semiconductor body;

<sup>1</sup>A marked-up copy of the amended portion of the claims is attached hereto.